ELPIDA

DATA SHEET

512MB Registered DDR SDRAM DIMM

HB54A5129F1U-B75B/10B (64M words × 72 bits, 1 Rank)

Description

The HB54A5129F1U is a 64M × 72 × 1 rank Double Data Rate (DDR) SDRAM Module, mounting 18 pieces of 256Mbits DDR SDRAM sealed in TSOP package, 1 piece of PLL clock driver, 2 pieces of register driver and 1 piece of serial EEPROM (2k bits EEPROM) for Presence Detect (PD). Read and write operations are performed at the cross points of the CK and the /CK. This high-speed data transfer is realized by the 2-bit prefetch-pipelined architecture. Data strobe (DQS) both for read and write are available for high speed and reliable data bus design. By setting extended mode register, the on-chip Delay Locked Loop (DLL) can be set enable or disable. An outline of the products is 184-pin socket type package (dual lead out). Therefore, it makes high density mounting possible without surface mount technology. It provides common data inputs and outputs. Decoupling capacitors are mounted beside each TSOP on the module board.

Features

- 184-pin socket type package (dual lead out)
  - Outline: 133.35mm (Length) × 30.48mm (Height) × 4.00mm (Thickness)
  - Lead pitch: 1.27mm
- 2.5V power supply (VCC/VCCQ)
- SSTL-2 interface for all inputs and outputs
- Clock frequency: 133MHz/125MHz (max.)
- Data inputs and outputs are synchronized with DQS
- 4 banks can operate simultaneously and independently (Component)
- Burst read/write operation
- Programmable burst length: 2, 4, 8
  - Burst read stop capability
- Programmable burst sequence
  - Sequential
  - Interleave
- Start addressing capability
  - Even and Odd
- Programmable /CAS latency (CL): 3, 3.5
- 8192 refresh cycles: 7.8µs (8192/64ms)
- 2 variations of refresh
  - Auto refresh
  - Self refresh

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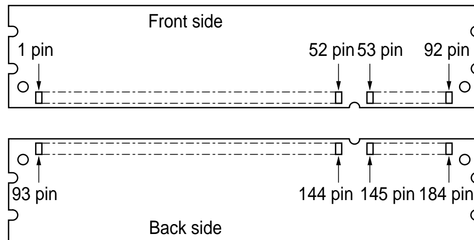
Ordering Information

Part number	Clock frequency MHz (max.)	/CE latency	Package	Contact pad
HB54A5129F1U-B75B*[1]	133	3.5	184-pin dual lead out socket type	Gold
HB54A5129F1U-10B*[2]	100	3.0		

Notes: 1. 100MHz operation at /CAS latency = 3.0.
2.125MHz operation at /CAS latency = 3.5.

Pin Configurations



Pin No.	Pin name	Pin No.	Pin name	Pin No.	Pin name	Pin No.	Pin name
1	VREF	47	DQS8	93	VSS	139	VSS
2	DQ0	48	A0	94	DQ4	140	DM8/DQS17
3	VSS	49	CB2	95	DQ5	141	A10
4	DQ1	50	VSS	96	VCCQ	142	CB6
5	DQS0	51	CB3	97	DM0/DQS9	143	VCCQ
6	DQ2	52	BA1	98	DQ6	144	CB7
7	VCC	53	DQ32	99	DQ7	145	VSS
8	DQ3	54	VCCQ	100	VSS	146	DQ36
9	NC	55	DQ33	101	NC	147	DQ37
10	/RESET	56	DQS4	102	NC	148	VCC
11	VSS	57	DQ34	103	NC	149	DM4/DQS13
12	DQ8	58	VSS	104	VCCQ	150	DQ38
13	DQ9	59	BA0	105	DQ12	151	DQ39
14	DQS1	60	DQ35	106	DQ13	152	VSS
15	VCCQ	61	DQ40	107	DM1/DQS10	153	DQ44
16	NC	62	VCCQ	108	VCC	154	/RAS
17	NC	63	/WE	109	DQ14	155	DQ45
18	VSS	64	DQ41	110	DQ15	156	VCCQ
19	DQ10	65	/CAS	111	NC	157	/S0
20	DQ11	66	VSS	112	VCCQ	158	NC
21	CKE0	67	DQS5	113	NC	159	DM5/DQS14
22	VCCQ	68	DQ42	114	DQ20	160	VSS
23	DQ16	69	DQ43	115	A12	161	DQ46
24	DQ17	70	VCC	116	VSS	162	DQ47
25	DQS2	71	NC	117	DQ21	163	NC
26	VSS	72	DQ48	118	A11	164	VCCQ
27	A9	73	DQ49	119	DM2/DQS11	165	DQ52
28	DQ18	74	VSS	120	VCC	166	DQ53
29	A7	75	NC	121	DQ22	167	NC
30	VCCQ	76	NC	122	A8	168	VCC

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Pin No.	Pin name	Pin No.	Pin name	Pin No.	Pin name	Pin No.	Pin name
31	DQ19	77	VCCQ	123	DQ23	169	DM6/DQS15
32	A5	78	DQS6	124	VSS	170	DQ54
33	DQ24	79	DQ50	125	A6	171	DQ55
34	VSS	80	DQ51	126	DQ28	172	VCCQ
35	DQ25	81	VSS	127	DQ29	173	NC
36	DQS3	82	VCCID	128	VCCQ	174	DQ60
37	A4	83	DQ56	129	DM3/DQS12	175	DQ61
38	VCC	84	DQ57	130	A3	176	VSS
39	DQ26	85	VCC	131	DQ30	177	DM7/DQS16
40	DQ27	86	DQS7	132	VSS	178	DQ62
41	A2	87	DQ58	133	DQ31	179	DQ63
42	VSS	88	DQ59	134	CB4	180	VCCQ
43	A1	89	VSS	135	CB5	181	SA0
44	CB0	90	NC	136	VCCQ	182	SA1
45	CB1	91	SDA	137	CK0	183	SA2
46	VCC	92	SCL	138	/CK0	184	VCCSPD

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Pin Description

Pin name	Function
A0 to A12	Address input Row address A0 to A12 Column address A0 to A9, A11
BA0, BA1	Bank select address
DQ0 to DQ63	Data input/output
CB0 to CB7	Check bit (Data input/output)
/RAS	Row address strobe command
/CAS	Column address strobe command
/WE	Write enable
/S0	Chip select
CKE0	Clock enable
CK0	Clock input
/CK0	Differential clock input
DQS0 to DQS8	Input and output data strobe
DM0 to DM8/DQS9 to DQS17	Input and output data strobe
SCL	Clock input for serial PD
SDA	Data input/output for serial PD
SA0 to SA2	Serial address input
VCC	Power for internal circuit
VCCQ	Power for DQ circuit
VCCSPD	Power for serial EEPROM
VREF	Input reference voltage
VSS	Ground
VCCID	VCC identification flag
/RESET	Reset pin (forces register inputs low)
NC	No connection

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Serial PD Matrix*[1]

Byte No.	Function described	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	Hex value	Comments
0	Number of bytes utilized by module manufacturer	1	0	0	0	0	0	0	0	80	128
1	Total number of bytes in serial PD device	0	0	0	0	1	0	0	0	08	256 byte
2	Memory type	0	0	0	0	0	1	1	1	07	SDRAM DDR
3	Number of row address	0	0	0	0	1	1	0	1	0D	13
4	Number of column address	0	0	0	0	1	0	1	1	0B	11
5	Number of DIMM ranks	0	0	0	0	0	0	0	1	01	1
6	Module data width	0	1	0	0	1	0	0	0	48	72 bits
7	Module data width continuation	0	0	0	0	0	0	0	0	00	0 (+)
8	Voltage interface level of this assembly	0	0	0	0	0	1	0	0	04	SSTL 2.5V
9	DDR SDRAM cycle time, CL = X -B75B	0	1	1	1	0	1	0	1	75	CL = 2.5*[5]
	-10B	1	0	0	0	0	0	0	0	80	
10	SDRAM access from clock (tAC) -B75B	0	1	1	1	0	1	0	1	75	0.75ns*[5]
	-10B	1	0	0	0	0	0	0	0	80	0.8ns*[5]
11	DIMM configuration type	0	0	0	0	0	0	1	0	02	ECC
12	Refresh rate/type	1	0	0	0	0	0	1	0	82	7.8 μs Self refresh
13	Primary SDRAM width	0	0	0	0	0	1	0	0	04	× 4
14	Error checking SDRAM width	0	0	0	0	0	1	0	0	04	× 4
15	SDRAM device attributes: Minimum clock delay back-to-back column access	0	0	0	0	0	0	0	1	01	1 CLK
16	SDRAM device attributes: Burst length supported	0	0	0	0	1	1	1	0	0E	2, 4, 8
17	SDRAM device attributes: Number of banks on SDRAM device	0	0	0	0	0	1	0	0	04	4
18	SDRAM device attributes: /CAS latency	0	0	0	0	1	1	0	0	0C	2/2.5
19	SDRAM device attributes: /CS latency	0	0	0	0	0	0	0	1	01	0
20	SDRAM device attributes: /WE latency	0	0	0	0	0	0	1	0	02	1
21	SDRAM module attributes	0	0	1	0	0	1	1	0	26	Registered
22	SDRAM device attributes: General	1	1	0	0	0	0	0	0	C0	± 0.2V
23	Minimum clock cycle time at CLX - 0.5	1	0	1	0	0	0	0	0	A0	CL = 2*[5]
24	Maximum data access time (tAC) from clock at CLX - 0.5 -B75B	0	1	1	1	0	1	0	1	75	0.75ns*[5]
	-10B	1	0	0	0	0	0	0	0	80	0.8ns*[5]
25	Minimum clock cycle time at CLX - 1	0	0	0	0	0	0	0	0	00	
26	Maximum data access time (tAC) from clock at CLX - 1	0	0	0	0	0	0	0	0	00	
27	Minimum row precharge time (tRP)	0	1	0	1	0	0	0	0	50	20ns
28	Minimum row active to row active delay (tRRD)	0	0	1	1	1	1	0	0	3C	15ns
29	Minimum /RAS to /CAS delay (tRCD)	0	1	0	1	0	0	0	0	50	20ns

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Byte No.	Function described	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	Hex value	Comments
30	Minimum active to precharge time (tRAS) -B75B	0	0	1	0	1	1	0	1	2D	45ns
	-10B	0	0	1	1	0	0	1	0	32	50ns
31	Module rank density	1	0	0	0	0	0	0	0	80	1 rank 512MB
32	Address and command setup time before clock (tIS) -B75B	1	0	0	1	0	0	0	0	90	0.9ns*5
	-10B	1	0	1	1	0	0	0	0	B0	1.1ns*5
33	Address and command hold time after clock (tIH) -B75B	1	0	0	1	0	0	0	0	90	0.9ns*5
	-10B	1	0	1	1	0	0	0	0	B0	1.1ns*5
34	Data input setup time before clock (tDS) -B75B	0	1	0	1	0	0	0	0	50	0.5ns*5
	-10B	0	1	1	0	0	0	0	0	60	0.6ns*5
35	Data input hold time after clock (tDH) -B75B	0	1	0	1	0	0	0	0	50	0.5ns*5
	-10B	0	1	1	0	0	0	0	0	60	0.6ns*5
36 to 40	Superset information	0	0	0	0	0	0	0	0	00	Future use
41	Active command period (tRC) -B75B	0	1	0	0	0	0	0	1	41	65ns*5
	-10B	0	1	0	0	0	1	1	0	46	70ns*5
42	Auto refresh to active/ Auto refresh command cycle (tRFC) -B75B	0	1	0	0	1	0	1	1	4B	75ns*5
	-10B	0	1	0	1	0	0	0	0	50	80ns*5
43	SDRAM tCK cycle max. (tCK max.)	0	0	1	1	0	0	0	0	30	12ns*5
44	Dout to DQS skew -B75B	0	0	1	1	0	0	1	0	32	500ps*5
	-10B	0	0	1	1	1	1	0	0	3C	600ps*5
45	Data hold skew (tQHS) -B75B	0	1	1	1	0	1	0	1	75	750ps*5
	-10B	1	0	1	0	0	0	0	0	A0	1000ps*5
46 to 61	Superset information	0	0	0	0	0	0	0	0	00	Future use
62	SPD revision	0	0	0	0	0	0	0	0	00	Initial
63	Checksum for bytes 0 to 62 -B75B	0	0	1	1	0	0	1	1	33	51
	-10B	1	1	1	1	1	0	0	0	F8	248
64	Manufacturer's JEDEC ID code	0	0	0	0	0	1	1	1	07	HITACHI
65 to 71	Manufacturer's JEDEC ID code	0	0	0	0	0	0	0	0	00	
72	Manufacturing location	×	×	×	×	×	×	×	×	××	*2 (ASCII-8bit code)
73	Module part number	0	1	0	0	1	0	0	0	48	H
74	Module part number	0	1	0	0	0	0	1	0	42	B
75	Module part number	0	0	1	1	0	1	0	1	35	5
76	Module part number	0	0	1	1	0	1	0	0	34	4
77	Module part number	0	1	0	0	0	0	0	1	41	A
78	Module part number	0	0	1	1	0	1	0	1	35	5
79	Module part number	0	0	1	1	0	0	0	1	31	1

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Byte No.	Function described	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	Hex value	Comments
80	Module part number	0	0	1	1	0	0	1	0	32	2
81	Module part number	0	0	1	1	1	0	0	1	39	9
82	Module part number	0	1	0	0	0	1	1	0	46	F
83	Module part number	0	0	1	1	0	0	0	1	31	1
84	Module part number	0	1	0	1	0	1	0	1	55	U
85	Module part number	0	0	1	0	1	1	0	1	2D	—
86	Module part number -B75B	0	1	0	0	0	0	1	0	42	B
	-10B	0	0	1	1	0	0	0	1	31	1
87	Module part number -B75B	0	0	1	1	0	1	1	1	37	7
	-10B	0	0	1	1	0	0	0	0	30	0
88	Module part number -B75B	0	0	1	1	0	1	0	1	35	5
	-10B	0	1	0	0	0	0	1	0	42	B
89	Module part number -B75B	0	1	0	0	0	0	1	0	42	B
	-10B	0	0	1	0	0	0	0	0	20	(Space)
90	Module part number	0	0	1	0	0	0	0	0	20	(Space)
91	Revision code	0	0	1	1	0	0	0	0	30	Initial
92	Revision code	0	0	1	0	0	0	0	0	20	(Space)
93	Manufacturing date	×	×	×	×	×	×	×	×	××	Year code (BCD)
94	Manufacturing date	×	×	×	×	×	×	×	×	××	Week code (BCD)
95 to 98	Module serial number	*3									
99 to 127	Manufacturer specific data	*4									

Notes: 1. All serial PD data are not protected. 0: Serial data, “driven Low”, 1: Serial data, “driven High”

2. Byte72 is manufacturing location code. (ex: In case of Japan, byte72 is 4AH. 4AH shows “J” on ASCII code.)
3. Bytes 95 through 98 are assembly serial number.
4. All bits of 99 through 127 are not defined (“1” or “0”).
5. These specifications are defined based on component specification, not module.

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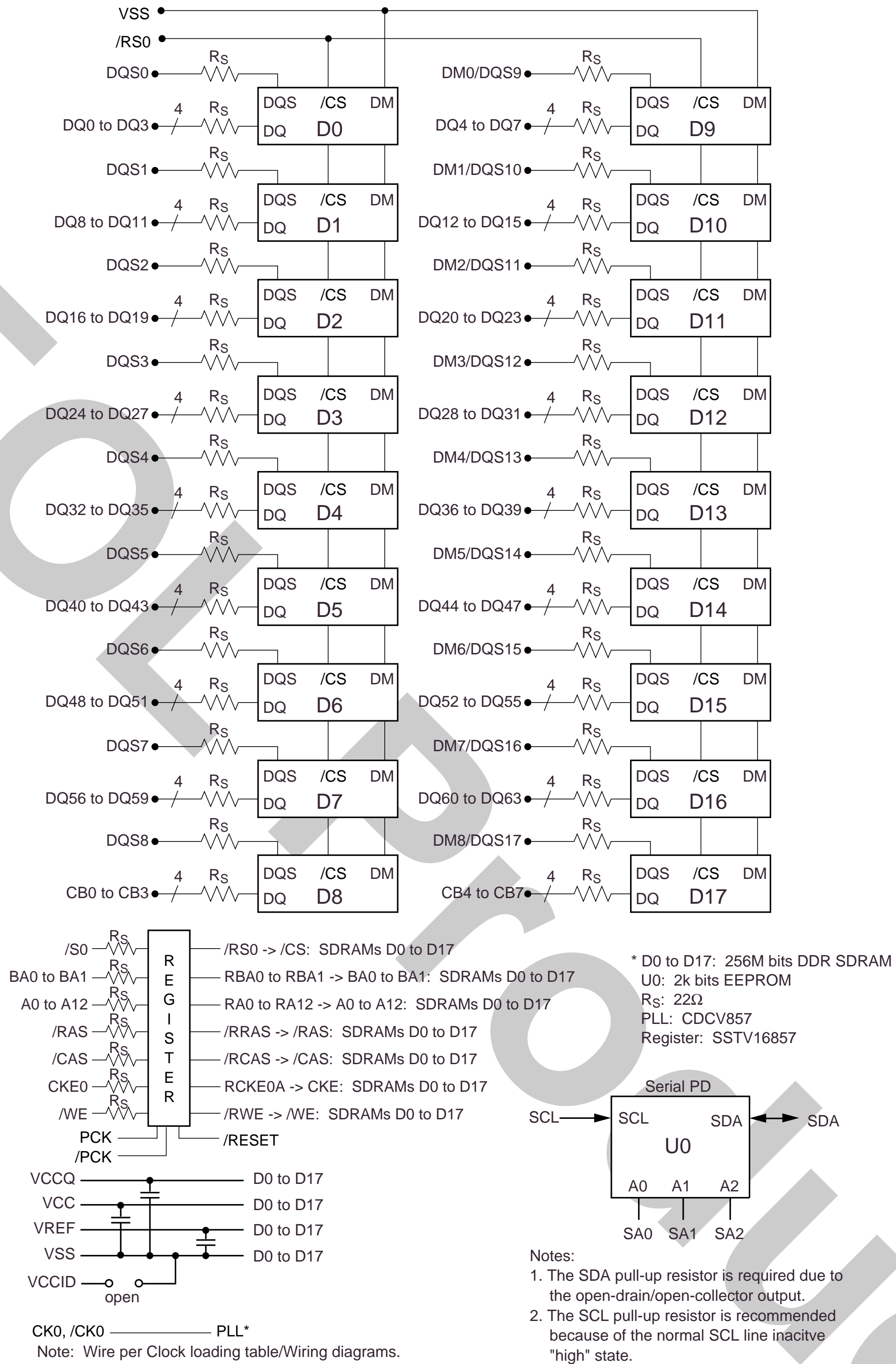
Block Diagram



Notes:
1. The SDA pull-up resistor is required due to the open-drain/open-collector output.
2. The SCL pull-up resistor is recommended because of the normal SCL line inacitve "high" state.

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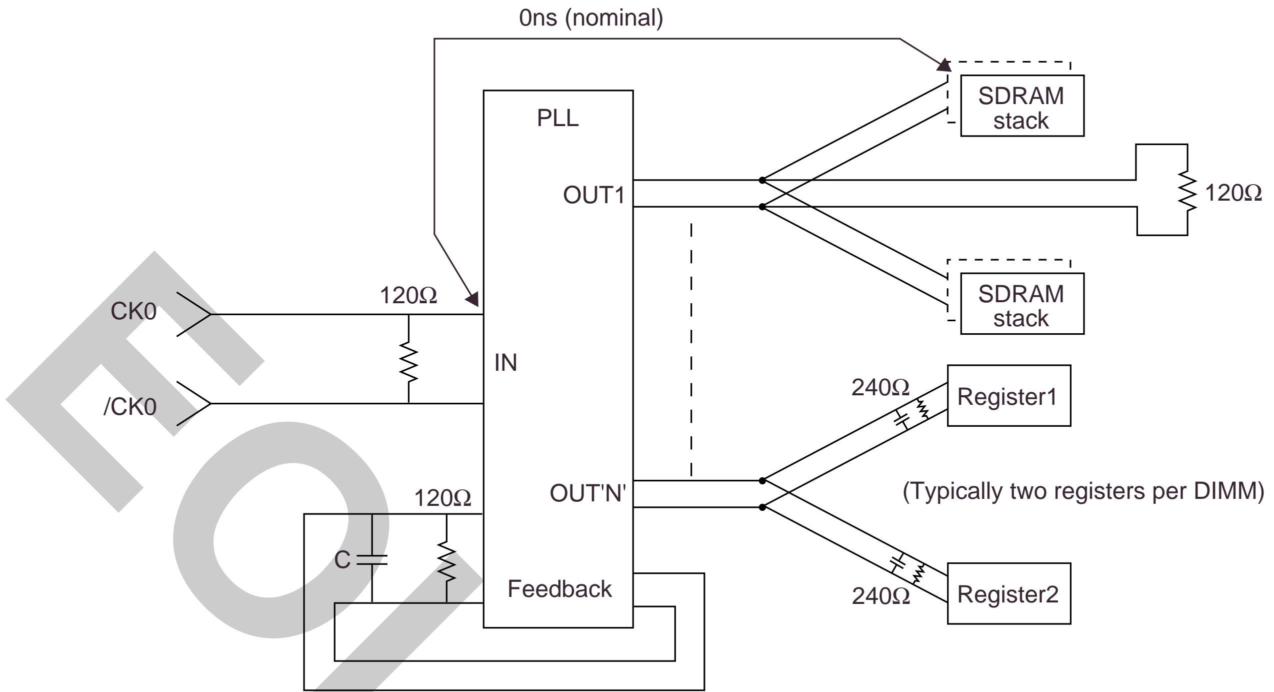
Differential Clock Net Wiring (CK0, /CK0)



Notes:
1. The clock delay from the input of the PLL clock to the input of any SDRAM or register willl be set to 0 ns (nominal).
2. Input, output and feedback clock lines are terminated from line to line as shown, and not from line to ground.
3. Only one PLL output is shown per output type. Any additional PLL outputs will be wired in a similar manner.
4. Termination resistors for feedback path clocks are located after the pins of the PLL.

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Pin Functions (1)

CK (CLK), /CK (/CLK) (input pin): The CK and the /CK are the master clock inputs. All inputs except DMs, DQSs and DQs are referred to the cross point of the CK rising edge and the VREF level. When a read operation, DQSs and DQs are referred to the cross point of the CK and the /CK. When a write operation, DMs and DQs are referred to the cross point of the DQS and the VREF level. DQSs for write operation are referred to the cross point of the CK and the /CK.

/S (/CS) (input pin): When /S is Low, commands and data can be input. When /S is High, all inputs are ignored. However, internal operations (bank active, burst operations, etc.) are held.

/RAS, /CAS, and /WE (input pins): These pins define operating commands (read, write, etc.) depending on the combinations of their voltage levels. See "Command operation".

A0 to A12 (input pins): Row address (AX0 to AX12) is determined by the A0 to the A12 level at the cross point of the CK rising edge and the VREF level in a bank active command cycle. Column address (AY0 to AY9, AY11) is loaded via the A0 to the A9, the A11 at the cross point of the CK rising edge and the VREF level in a read or a write command cycle. This column address becomes the starting address of a burst operation.

A10 (AP) (input pin): A10 defines the precharge mode when a precharge command, a read command or a write command is issued. If A10 = High when a precharge command is issued, all banks are precharged. If A10 = Low when a precharge command is issued, only the bank that is selected by BA1, BA0 is precharged. If A10 = High when read or write command, auto-precharge function is enabled. While A10 = Low, auto-precharge function is disabled.

BA0, BA1 (input pin): BA0/BA1 are bank select signals. The memory array is divided into bank 0, bank 1, bank 2 and bank 3. If BA1 = Low and BA0 = Low, bank 0 is selected. If BA1 = High and BA0 = Low, bank 1 is selected. If BA1 = Low and BA0 = High, bank 2 is selected. If BA1 = High and BA0 = High, bank 3 is selected.

CKE (input pin): CKE controls power down and self-refresh. The power down and the self-refresh commands are entered when the CKE is driven Low and exited when it resumes to High.

The CKE level must be kept for 1 CK cycle (= LCKEPW) at least, that is, if CKE changes at the cross point of the CK rising edge and the VREF level with proper setup time tIS, at the next CK rising edge CKE level must be kept with proper hold time tIH.

Pin Functions (2)

DQ, CB (input and output pins): Data are input to and output from these pins.

DQS (input and output pin): DQS provide the read data strobes (as output) and the write data strobes (as input).

VCC and VCCQ (power supply pins): 2.5V is applied. (VCC is for the internal circuit and VCCQ is for the output buffer.)

VCCSPD (power supply pin): 2.5V is applied (For serial EEPROM).

VSS (power supply pin): Ground is connected.

/RESET (input pin): LVCMOS reset input. When /RESET is low, all registers are reset and all outputs are low.

Detailed Operation Part, AC Characteristics and Timing Waveforms

Refer to the HM5425161B/HM5425801B/HM5425401B Series datasheet (E0086H). DM pins of component device fixed to VSS level on the module board. DIMM /CAS latency = Device CL + 1 for registered type.

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Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	Note
Voltage on any pin relative to VSS	VT	–1.0 to +4.6	V	1
Supply voltage relative to VSS	VCC, VCCQ	–1.0 to +4.6	V	1
Short circuit output current	IOUT	50	mA	
Power dissipation	PT	18	W	
Operating ambient temperature	TA	0 to +70	°C	2
Storage temperature	Tstg	–50 to +100	°C	

Notes: 1. Respect to VSS.
2. DDR SDRAM component specification.

DC Operating Conditions (TA = 0 to +70°C) (DDR SDRAM Component Specification)

Parameter	Symbol	min.	Typ	max.	Unit	Notes
Supply voltage	VCC, VCCQ	2.3	2.5	2.7	V	1, 2
	VSS	0	0	0	V	
Input reference voltage	VREF	1.15	1.25	1.35	V	1
Termination voltage	VTT	VREF – 0.04	VREF	VREF + 0.04	V	1
DC Input high voltage	VIH	VREF + 0.18	—	VCCQ + 0.3	V	1, 3
DC Input low voltage	VIL	–0.3	—	VREF – 0.18	V	1, 4
DC Input signal voltage	VIN (DC)	–0.3	—	VCCQ + 0.3	V	5
DC differential input voltage	VSWING (DC)	0.36	—	VCCQ + 0.6	V	6

Notes: 1. All parameters are referred to VSS, when measured.
2. VCCQ must be lower than or equal to VCC.
3. VIH is allowed to exceed VCC up to 4.6V for the period shorter than or equal to 5ns.
4. VIL is allowed to outreach below VSS down to –1.0V for the period shorter than or equal to 5ns.
5. VIN (DC) specifies the allowable DC execution of each differential input.
6. VSWING (DC) specifies the input differential voltage required for switching.

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DC Characteristics 1 (TA = 0 to +70°C, VCC, VCCQ = 2.5V ± 0.2V, VSS = 0V)

Parameter	Symbol	Grade	max.	Unit	Test condition	Notes
Operating current (ACTV-PRE)	ICC0	-B75B -10B	2096 1819	mA	CKE ≥ VIH, tRC = min.	1, 2, 5
Operating current (ACTV-READ-PRE)	ICC1	-B75B -10B	2996 2719	mA	CKE ≥ VIH, BL = 2, CL = 3.5, tRC = min.	1, 2, 5
Idle power down standby current	ICC2P	-B75B -10B	656 595	mA	CKE ≤ VIL	4
Idle standby current	ICC2N	-B75B -10B	1016 919	mA	CKE ≥ VIH, /CS ≥ VIH	4
Active power down standby current	ICC3P	-B75B -10B	746 649	mA	CKE ≤ VIL	3
Active standby current	ICC3N	-B75B -10B	1196 1099	mA	CKE ≥ VIH, /CS ≥ VIH tRAS = max.	3
Operating current (Burst read operation)	ICC4R	-B75B -10B	4256 4069	mA	CKE ≥ VIH, BL = 2, CL = 3.5	1, 2, 5, 6
Operating current (Burst write operation)	ICC4W	-B75B -10B	3896 3709	mA	CKE ≥ VIH, BL = 2, CL = 3.5	1, 2, 5, 6
Auto refresh current	ICC5	-B75B -10B	3986 3619	mA	tRFC = min., Input ≤ VIL or ≥ VIH	
Self refresh current	ICC6	-B75B -10B	440 433	mA	Input ≥ VCC – 0.2V Input ≤ 0.2V.	

Notes. 1. These ICC data are measured under condition that DQ pins are not connected.
2. One bank operation.
3. One bank active.
4. All banks idle.
5. Command/Address transition once per one cycle.
6. Data/Data mask transition twice per one cycle.
7. The ICC data on this table are measured with regard to tCK = min. in general.

DC Characteristics 2 (TA = 0 to +70°C, VCC, VCCQ = 2.5V ± 0.2V, VSS = 0V)

Parameter	Symbol	min.	max.	Unit	Test condition	Notes
Input leakage current	ILI	–10	10	µA	VCC ≥ VIN ≥ VSS	
Output leakage current	ILO	–10	10	µA	VCC ≥ VOUT ≥ VSS	
Output high voltage	VOH	1.95	—	V	IOH (max.) = –15.2mA	1
Output low voltage	VOL	—	0.35	V	IOL (min.) = 15.2mA	1

Note: 1.DDR SDRAM component specification.

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Pin Capacitance (TA = 25°C, VCC, VCCQ = 2.5V ± 0.2V)

Parameter	Symbol	Pins	max.	Unit	Notes
Input capacitance	CI1	Address, /RAS, /CAS, /WE, /S, CKE	10	pF	1, 3
Input capacitance	CI2	CK, /CK	20	pF	1, 3
Data and DQS input/output capacitance	CO	DQ, DQS, CB	15	pF	1, 2, 3

Notes: 1. These parameters are measured on conditions: f = 100MHz, VOUT = VCCQ/2, ΔVOUT = 0.2V.
2. Dout circuits are disabled.
3. This parameter is sampled and not 100% tested.

Timing Parameter Measured in Clock Cycle for Registered DIMM

		Number of clock cycle		
Parameter	Symbol	min.	max.	Unit.
Write to pre-charge command delay (same bank)	tWPD	3 + BL/2		tCK
Read to pre-charge command delay (same bank)	tRPD	BL/2		tCK
Write to read command delay (to input all data)	tWRD	2 + BL/2		tCK
Burst stop command to write command delay (CL = 3)	tBSTW	2		tCK
(CL = 3.5)	tBSTW	3		tCK
Burst stop command to DQ High-Z (CL = 3)	tBSTZ	3		tCK
(CL = 3.5)	tBSTZ	3.5		tCK
Read command to write command delay (to output all data) (CL = 3)	tRWD	2 + BL/2		tCK
(CL = 3.5)	tRWD	3 + BL/2		tCK
Pre-charge command to High-Z (CL = 3)	tHZP	3		tCK
(CL = 3.5)	tHZP	3.5		tCK
Write command to data in latency	tWCD	2		tCK
Write recovery	tWR	1		tCK
Register set command to active or register set command	tMRD	2		tCK
Self refresh exit to non-read command	tSNR	10		tCK
Self refresh exit to read command	tSRD	200		tCK
Power down entry	tPDEN	1		tCK
Power down exit to command input	tPDEX	1		tCK
CKE minimum pulse width	tCKEPW	1		tCK

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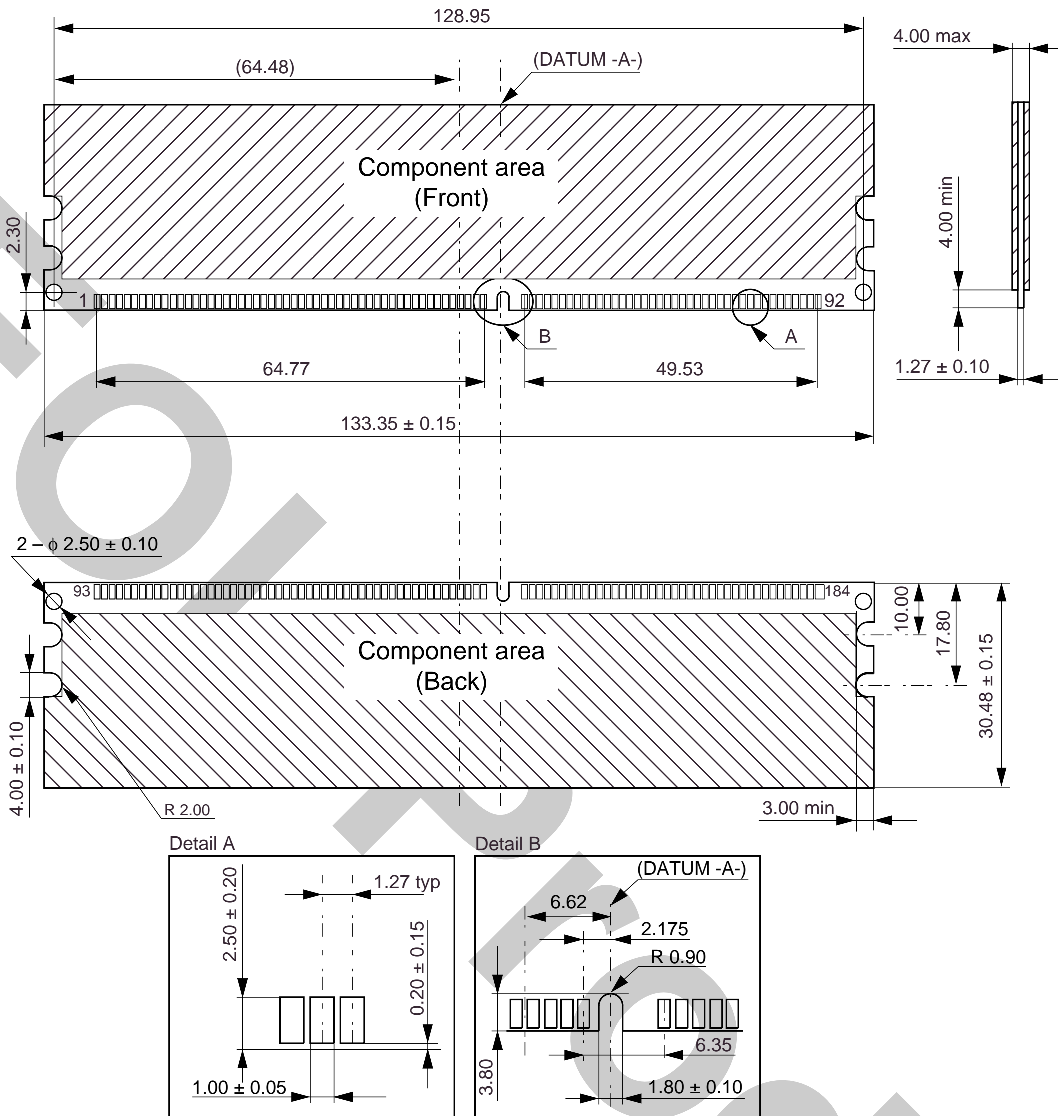
Physical Outline



Note: Tolerance on all dimensions ± 0.13 unless otherwise specified.

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CAUTION FOR HANDLING MEMORY MODULES

When handling or inserting memory modules, be sure not to touch any components on the modules, such as the memory ICs, chip capacitors and chip resistors. It is necessary to avoid undue mechanical stress on these components to prevent damaging them.
In particular, do not push module cover or drop the modules in order to protect from mechanical defects, which would be electrical defects.

When re-packing memory modules, be sure the modules are not touching each other.
Modules in contact with other modules may cause excessive mechanical stress, which may damage the modules.

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NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR MOS DEVICES

Exposing the MOS devices to a strong electric field can cause destruction of the gate oxide and ultimately degrade the MOS devices operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it, when once it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. MOS devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. MOS devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor MOS devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS DEVICES

No connection for CMOS devices input pins can be a cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. The unused pins must be handled in accordance with the related specifications.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Power-on does not necessarily define initial status of MOS devices. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the MOS devices with reset function have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. MOS devices are not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for MOS devices having reset function.

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